
FOREWORD

Special Section on Fundamentals and Applications of Advanced Semiconductor Devices

This special section is compiled every year focusing on fundamentals and application of advanced semiconductor devices. This section consists of impressive papers related to a fabrication of ferroelectric gate field effect transistor, interface properties of particular silicide on silicon, a doped thin film formation technology, simulations of gallium nitride based high electron mobility transistors. I deeply appreciate their contributions.

On the other hand, candidly, the total number of papers for the section is recently decreased. It is easy to try to find the reason of decreasing to the change of world and era, however, we have to watch carefully and analyze the fact towards considering how we continuously proceed to activate incentives for contributors in the related field of the fundamentals and application of advanced semiconductor devices.

I would like to deeply express my thanks to all authors for their contributions to the special section. I also thank all reviewers and editorial committee members for their irreplaceable contributions to the review and editing processes.

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Michihiko Suhara (*Member*) received the B.S., M.S., and Ph.D. degrees in the Electrical and Computer Engineering from Kanazawa University, Kanazawa, Japan, in 1988, 1990 and 1993, respectively. In 1993, he joined Department of the Electrical and Electronics Engineering, Tokyo Research Center for Quantum Effect Electronics, Tokyo Institute of Technology, Japan, as a research associate. In 1997, and from 1998 to 1999, he was with Department of Solid State Physics, University of Lund, Sweden as a visiting scientist and a visiting professor, respectively. In 1999, he joined Department Electrical Engineering, Tokyo Metropolitan University, Japan as an Associate Professor. Since 2010, he has been a Professor of Department of the Electrical and Electronic Engineering, Tokyo Metropolitan University and he is currently working on semiconductor quantum devices. He served as chair of the Electron Devices (ED) Technical Committee of IEICE from 2019.

